MOSFETs Silicon N-Channel MOS (DTMOSIV)

# TK62J60W

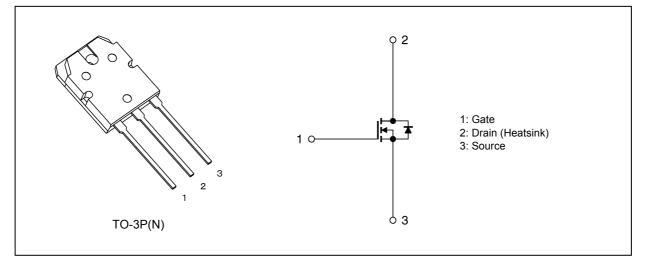
#### 1. Applications

Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 0.033 \Omega$  (typ.) by used to Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode:  $V_{th}$  = 2.7 to 3.7 V ( $V_{\rm DS}$  = 10 V,  $I_{\rm D}$  = 3.1 mA)

#### 3. Packaging and Internal Circuit



#### 4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characteristics			Rating	Unit
Drain-source voltage		V <sub>DSS</sub>	600	V
Gate-source voltage		V <sub>GSS</sub>	±30	
Drain current (DC)	(Note 1)	I <sub>D</sub>	61.8	A
Drain current (pulsed)	(Note 1)	I <sub>DP</sub>	247	
Power dissipation (T <sub>c</sub> =	25°C)	PD	400	W
Single-pulse avalanche energy	(Note 2)	E <sub>AS</sub>	698	mJ
Avalanche current		I <sub>AR</sub>	15.5	A
Reverse drain current (DC)	(Note 1)	I <sub>DR</sub>	61.8	
Reverse drain current (pulsed)	(Note 1)	I <sub>DRP</sub>	247	
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	7
Mounting torque		TOR	0.8	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production 2012-09

#### 5. Thermal Characteristics

Characteristics		Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	0.313	°C/W
Channel-to-ambient thermal resistance	R <sub>th(ch-a)</sub>	50	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V\_DD = 90 V, T\_ch = 25°C (initial), L = 5.08 mH, R\_G = 25  $\Omega$ , I\_AR = 15.5 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

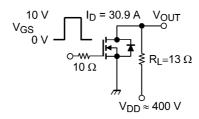
#### 6. Electrical Characteristics

#### 6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±30 V, $V_{DS}$ = 0 V	_	_	±1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 600 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	600	—	—	V
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3.1 mA	2.7	_	3.7	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 30.9 A		0.033	0.040	Ω

#### 6.2. Dynamic Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 300 V, V <sub>GS</sub> = 0 V, f = 100 kHz	_	6500	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	]	_	20	_	
Output capacitance	C <sub>oss</sub>		_	140	_	
Effective output capacitance	C <sub>o(er)</sub>	$V_{DS}$ = 0 to 400 V, $V_{GS}$ = 0 V	_	200	_	
Gate resistance	r <sub>g</sub>	V <sub>DS</sub> = OPEN, f = 1 MHz	_	2	_	Ω
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1	_	58	_	ns
Switching time (turn-on time)	t <sub>on</sub>	]	_	115	_	
Switching time (fall time)	t <sub>f</sub>	]	_	15	_	
Switching time (turn-off time)	t <sub>off</sub>	]	_	310		
MOSFET dv/dt ruggedness	dv/dt	V <sub>DD</sub> = 0 to 400 V, I <sub>D</sub> = 15.5 A	50	_	_	V/ns



Duty  $\leq$  1%,  $t_W^{}=$  10  $\mu s$ 

Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V},  V_{GS} \text{ = } 10  \text{V},  \text{I}_{D} \text{ = } 61.8  \text{A}$	—	180	_	nC
Gate-source charge 1	Q <sub>gs1</sub>		_	38	_	
Gate-drain charge	Q <sub>gd</sub>		_	85	_	

#### 6.4. Source-Drain Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V <sub>DSF</sub>	I <sub>DR</sub> = 61.8 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	t <sub>rr</sub>	I <sub>DR</sub> = 30.9 A, V <sub>GS</sub> = 0 V	_	500	_	ns
Reverse recovery charge	Q <sub>rr</sub>	-dI <sub>DR</sub> /dt = 50 A/μs	_	7	_	μC
Peak reverse recovery current	I <sub>rr</sub>		_	25	_	А
Diode dv/dt ruggedness	dv/dt	$I_{DR}$ = 30.9 A, $V_{GS}$ = 0 V, $V_{DD}$ = 400 V	15	_	_	V/ns

#### 7. Marking (Note)

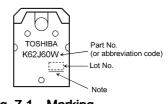
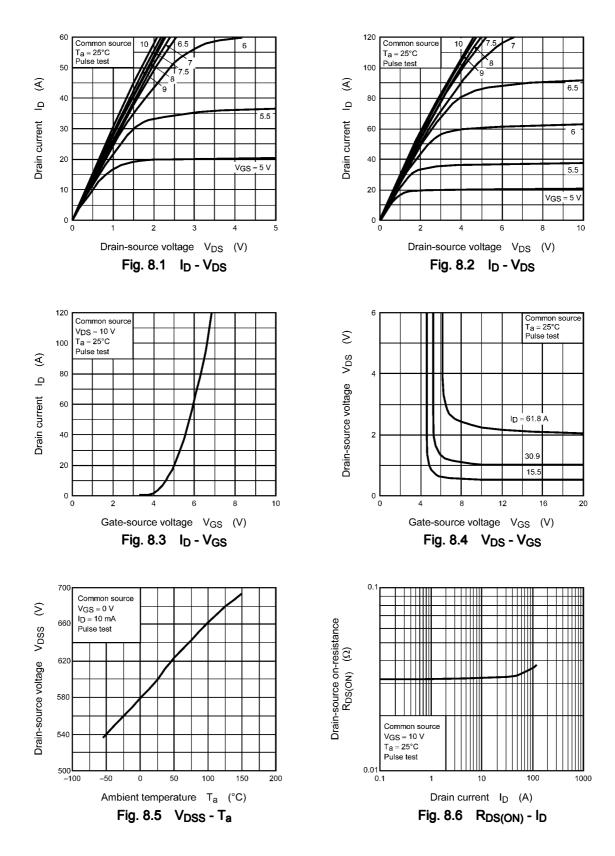
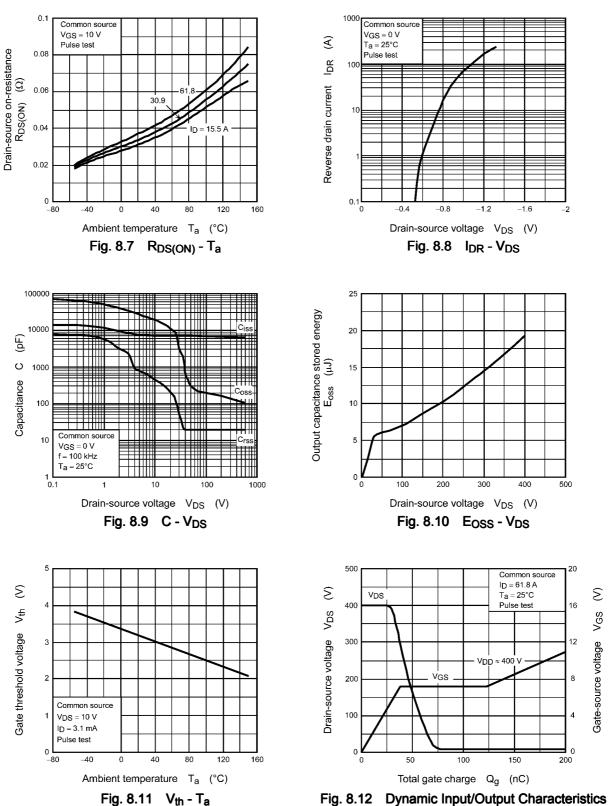


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]] Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

#### 8. Characteristics Curves (Note)





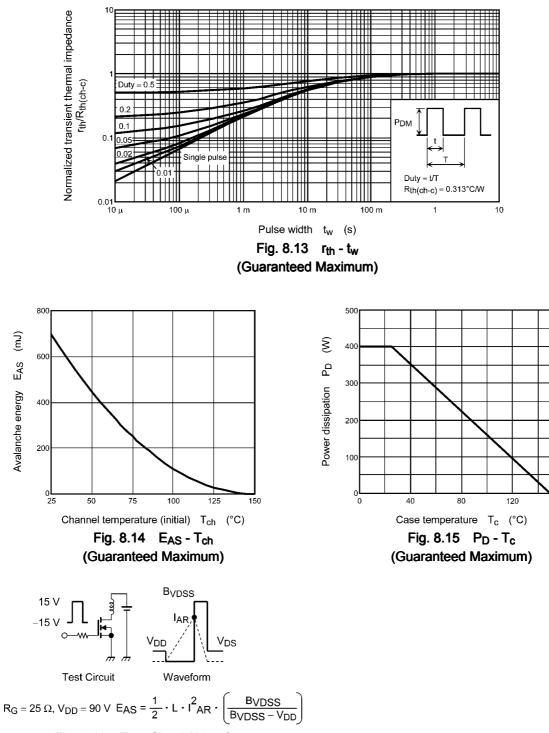
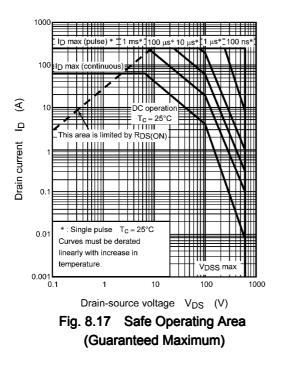


Fig. 8.16 Test Circuit/Waveform

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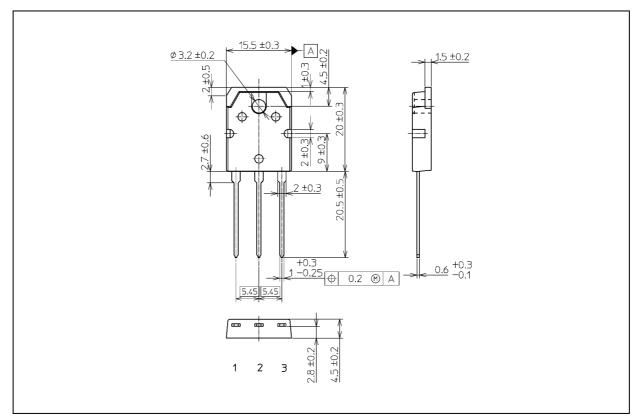


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

#### TK62J60W

#### Package Dimensions

Unit: mm



#### Weight: 4.6 g (typ.)

Package Name(s)	
JEITA: SC-65	
TOSHIBA: 2-16C1S	
Nickname: TO-3P(N)	

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